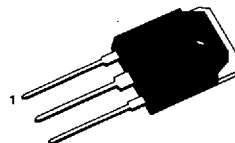


FEATURES

- Lower $R_{DS(on)}$
- Improved inductive ruggedness
- Fast switching times
- Rugged polysilicon gate cell structure
- Lower input capacitance
- Extended safe operating area
- Improved high temperature reliability

TO-3P



1. Gate 2. Drain 3. Source

PRODUCT SUMMARY

Part Number	BV_{DSS}	$R_{DS(on)}$	I_D
SSH6N60	600V	$1.8\ \Omega$	6A
SSH6N55	550V	$1.8\ \Omega$	6A

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	SSH6N60	SSH6N55	Unit
Drain-Source Voltage (1)	V_{DSS}	600	550	Vdc
Drain-Gate Voltage ($R_{GS}=1.0M\ \Omega$) (1)	V_{DGR}	600	550	Vdc
Gate-Source Voltage	V_{GS}	± 20		Vdc
Continuous Drain Current $T_c=25\ ^\circ C$	I_D	6.0		Adc
Continuous Drain Current $T_c=100\ ^\circ C$	I_D	4.0		Adc
Drain Current - Pulsed (3)	I_{DM}	24		Adc
Gate Current - Pulsed	I_{GM}	± 1.5		Adc
Single Pulsed Avalanche Energy (4)	EAS	570		mJ
Avalanche Current	I_{AS}	6.0		A
Total Power Dissipation at $T_c=25\ ^\circ C$	P_D	135		Watts
Derate above $25\ ^\circ C$		1.08		W/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to $+150$		$^\circ C$
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	T_L	300		$^\circ C$

Notes : (1) $T_J=25^\circ C$ to $150^\circ C$ (2) Pulse test : Pulse width $< 300\ \mu s$, Duty Cycle $< 2\%$

(3) Repetitive rating : Pulse width limited by junction temperature

(4) $L=27mH$, $V_{dd}=50V$, $R_G=25\ \Omega$, Starting $T_J=25^\circ C$

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
BV _{DS}	Drain-Source Breakdown Voltage					
	SSH6N60	600	-	-	V	V _{GS} =0V, I _D =250μA
	SSH6N55	550	-	-	V	
V _{GS(th)}	Gate Threshold Voltage	2.0	-	4.5	V	V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	Gate-Source Leakage Forward	-	-	100	nA	V _{GS} =20V
I _{GSS}	Gate-Source Leakage Reverse	-	-	-100	nA	V _{GS} =-20V
I _{DSS}	Zero Gate Voltage Drain Current	-	-	250	μA	V _{DS} =Max. Rating, V _{GS} =0V
		-	-	1000	μA	V _{DS} =0.8 Max. Rating, V _{GS} =0V, T _c =150°C
R _{DS(on)}	Static Drain-Source On-Resistance(2)	-	-	1.8	Ω	V _{GS} =10V, I _D =3.0A
g _{fs}	Forward Transconductance (2)	3.0	4.8	-	Ω	V _{DS} ≥ 50V, I _D =3.0A
C _{iss}	Input Capacitance	-	-	1800	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
C _{oss}	Output Capacitance	-	-	350	pF	
C _{rss}	Reverse Transfer Capacitance	-	125	150	pF	
t _{d(on)}	Turn-On Delay Time	-	-	60	ns	V _{DD} =0.5 BV _{DS} , I _D =6.0A, Z _o =9.1Ω (MOSFET switching times are essentially independent of operating temperature)
t _r	Rise Time	-	-	150	ns	
t _{d(off)}	Turn-Off Delay Time	-	-	200	ns	
t _f	Fall Time	-	-	120	ns	
Q _g	Total Gate Charge (Gate-Source Plus Gate-Drain)	-	-	77	nC	V _{GS} =10V, I _D =6.0A, V _{DS} =0.8 Max. Rating (Gate charge is essentially independent of operating temperature)
Q _{gs}	Gate-Source Charge	-	9.3	-	nC	
Q _{gd}	Gate-Drain ("Miller") Charge	-	29.3	-	nC	

THERMAL RESISTANCE

Symbol	Characteristics		All	Units	Remark
R _{thJC}	Junction-to-Case	MAX	0.93	K/W	
R _{thCS}	Case-to-Sink	TYP	0.24	K/W	Mounting surface flat
R _{thJA}	Junction-to-Ambient	MAX	40	K/W	Free Air Operation

Notes : (1) T_J=25°C to 150°C

(2) Pulse test : Pulse width < 300μs, Duty Cycle < 2%

(3) Repetitive rating : Pulse width limited by junction temperature

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	-	-	6.0	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier
I_{SM}	Pulse Source Current (Body Diode) (3)	-	-	24.0	A	
V_{SD}	Diode Forward Voltage (2)	-	-	1.5	V	$T_J = 25^\circ\text{C}$, $I_S = 6.0\text{A}$, $V_{GS} = 0\text{V}$
t_{rr}	Reverse Recovery Time	-	450	940	ns	$T_J = 25^\circ\text{C}$, $I_F = 6.0\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{S}$

Notes: (1) $T_J = 25^\circ\text{C}$ to 150°C (2) Pulse test: Pulse width $< 300\mu\text{s}$, Duty Cycle $< 2\%$

(3) Repetitive rating: Pulse width limited by junction temperature

